TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type ($L^2-\pi$ -MOSV)

2SK2614

Chopper Regulator, DC/DC Converter and Motor Drive Applications

- 4 V gate drive
- Low drain-source ON-resistance : $R_{DS (ON)} = 0.032 \Omega$ (typ.)
- High forward transfer admittance : |Y_{fs}| = 13S (typ.)
- Low leakage current : I_{DSS} = 100 µA (max) (V_{DS} = 50 V)
- Enhancement mode : V_{th} = 0.8~2.0 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

Character	istic	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	50	V	
Drain-gate voltage (R	_{GS} = 20 kΩ)	VDGR	50	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	20	А	
	Pulse (Note 1)	I _{DP}	50	А	
Drain power dissipatio	n (Tc = 25°C)	PD	40	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

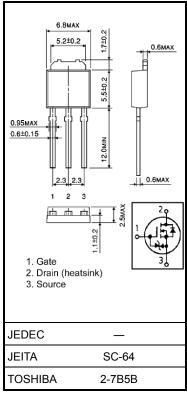
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

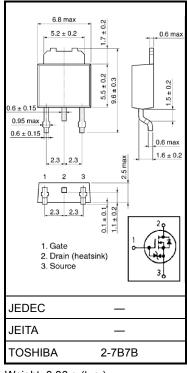
Thermal Characteristics

Characteristic	Symbol	Мах	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.125	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	125	°C / W

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.36 g (typ.)



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Unit: mm

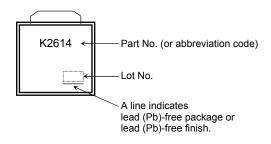
Electrical Characteristics (Ta = 25°C)

Charao	cteristic	Symbol	Test Condition	Min	Тур.	Мах	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	_	±10	μΑ
Drain cutoff current		I _{DSS}	V_{DS} = 50 V, V_{GS} = 0 V	_	-	100	μA
Drain-source breakdown voltage		V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	50	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	0.8	_	2.0	V
Drain-source ON-resistance		R _{DS (ON)}	V _{DS} = 4 V, I _D = 5 A	—	0.055	0.08	Ω
			V _{DS} = 10 V, I _D = 10 A	_	0.032	0.046	
Forward transfer	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 10 A	7	13	—	S
Input capacitance	citance C _{iss}			_	900	_	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	130	_	
Output capacitance		C _{oss}		_	370	_	
Switching time	Rise time	tr		_	15	_	
	Turn-on time	t _{on}		_	25	_	
	Fall time	t _f	V _{DD} ≈ 30 V	_	30	_	ns
	Turn-off time	t _{off}	Duty ≤ 1%, t _w = 10 μs	_	100	_	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ 40 V, V _{GS} = 10 V, I _D = 20 A	_	25	_	nC
Gate-source charge		Qgs		_	19	_	
Gate-drain ("Miller") charge		Q _{gd}		_	6	_	

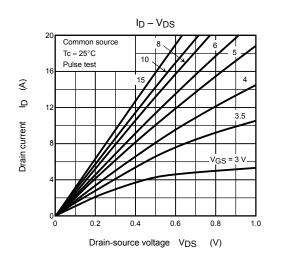
Source–Drain Ratings and Characteristics (Ta = 25°C)

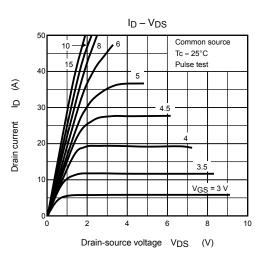
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	-	20	A
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	50	A
Forward voltage (diode)	V _{DSF}	I _{DR} = 20 A, V _{GS} = 0 V	—	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 20 A, V _{GS} = 0 V, dI _{DR} / dt = 50 A / μs	_	60	_	ns
Reverse recovery charge	Qrr			45	-	μC

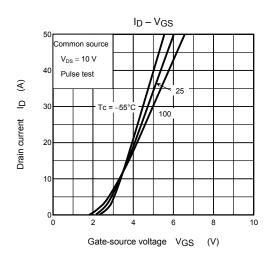
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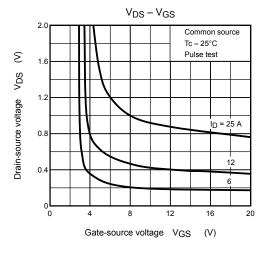


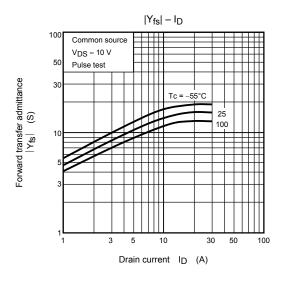
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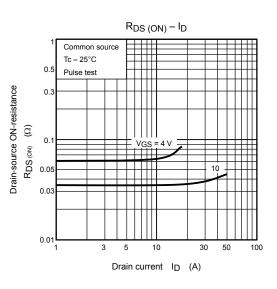




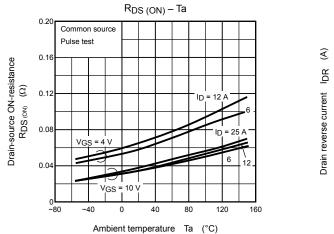


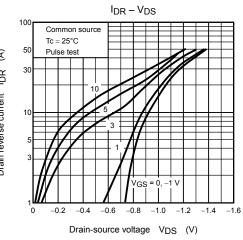


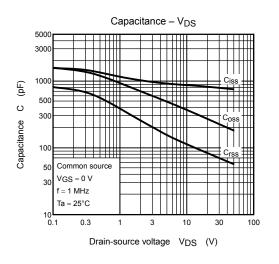


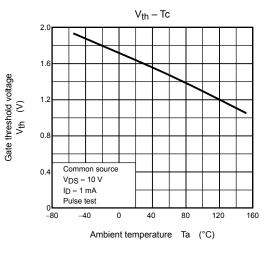


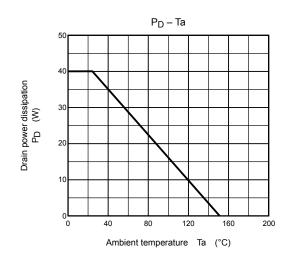
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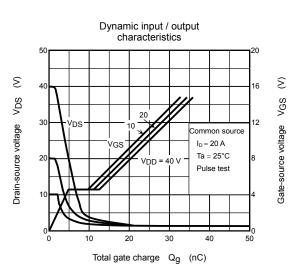


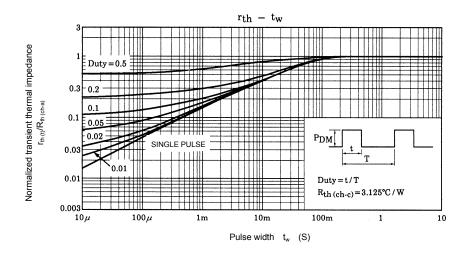


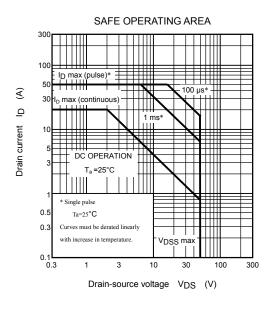












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